

IN THE CLAIMS

Please amend Claim 1 and add new Claims 33-42 as follows.

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1. (AMENDED) A method of etching a metallic film, comprising the steps of:
forming a metallic film on a thin film resistor;
forming a conductive film on the metallic film;
forming a first opening in the conductive film to expose the metallic film
from the first opening;
forming a mask on the conductive film after forming the first opening, the
mask having a second opening having an opening area smaller than that of the first
opening and open in the first opening to expose the metallic film therefrom; and
etching the metallic film through the second opening.

2. (PENDING) The method of Claim 1, wherein the step of etching the
metallic film includes steps of:
dry-etching a first part of the metallic film through the second opening; and
wet-etching a second part of the metallic film, the second part directly
contacting the thin film resistor.

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3. (PENDING) The method of Claim 1, wherein a side wall of the first
opening is entirely covered with the mask defining the second opening therein.

4. (PENDING) The method of Claim 1, wherein the step of forming the mask includes steps of:

forming a photo-resist on the conductive film and in the first opening to serve as the mask; and

removing a part of the photo-resist to form the second opening.

7. (PENDING) The method of Claim 2, wherein a thickness of the first part is equal to or larger than 20% relative to an entire thickness of the metallic film.

8. (PENDING) The method of Claim 2, wherein a thickness of the second part is equal to or larger than 100 Å.

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cont 9. (PENDING) The method of Claim 2, wherein the step of dry-etching the metallic film uses an etching gas including CF_4 .

10. (PENDING) The method of Claim 2, wherein the step of wet-etching the metallic film uses an etching solution including H_2O_2 .

11. (PENDING) The method of Claim 2, wherein the metallic film is formed with a thickness equal to or larger than 500 Å.

26. (PENDING) The method of Claim 2, wherein the metallic film is a single layer.

27. (PENDING) The method of Claim 2, wherein the metallic film is directly disposed on the thin film resistor.

33. (NEW) The method of Claim 1, wherein the mask is formed to cover a sidewall of the conductive film defining the first opening.

34. (NEW) A method of etching a metallic film, comprising:

- forming a metallic film;
- forming a conductive film on the metallic film, the conductive film being different substance from the metallic film;
- forming an opening in the conductive film to expose a sidewall of the conductive film and a portion of the underlying metallic film through the opening;
- forming a masking film over the conductive film, the masking film having a pattern which exposes a part of the portion of the metallic film in the opening with the sidewall of the conductive film covered; and
- etching the metallic film using the masking film as an etching mask, the etching including wet etching.

35. (NEW) The method of Claim 34, wherein an ionization tendency of the conductive film is larger than that of the metallic film.

36. (NEW) The method of Claim 34, further comprising, prior to the forming the metallic film, forming a resistive film, the conductive film being formed on the resistive film.

37. (NEW) The method of Claim 36, wherein the ionization tendency of the metallic film is larger than that of the metallic film.

38. (NEW) The method of Claim 37, wherein an ionization tendency of the conductive film is larger than that of the metallic film.

39. (NEW) The method of Claim 34, wherein a length of the masking film covering the metallic film in the opening is controlled in association with a side-etching amount of the metallic film during the etching.

40. (NEW) The method of Claim 38, wherein the length of the masking film covering the metallic film in the opening is controlled in association with a side-etching amount of the metallic film during the etching.

41. (NEW) The method of Claim 34, wherein the etching includes dry etching prior to the wet etching.

42. (NEW) The method of Claim 40, wherein the etching includes dry etching prior to the wet etching.